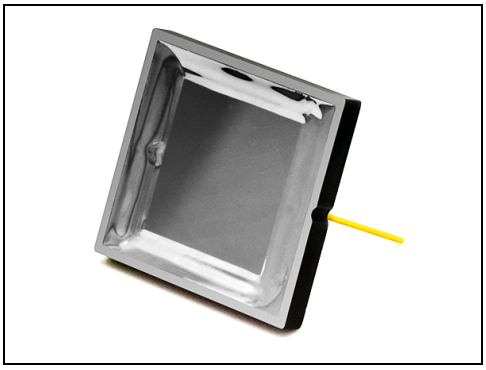
PHOTODIODE 100 mm^2 with Integrated Thin Film Filter — SXUV100TF135B



FEATURES

- 100 mm^2 Square Active Area
- Responsivity @ 13.5 nm 0.09 A/W
- Detection Range 12 nm to 18 nm
- Optimized for Zero Bias Operation
- High Shunt Resistance of 10Mohm
- Shipped with Protective Cover

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	10 mm x 10 mm		100		mm^2
Responsivity, $\mathcal{R}$	@13.5 nm	.08	.09	0.1	A/W
Shunt Resistance, Rsh	@±10mV	10			MΩ
Reverse Breakdown Voltage, V_R	1_R = 1 µA	20			Volts
Capacitance, C	V_R = 0 V		5	20	nF

THERMAL PARAMETERS

STORAGE AND OPERATION TEMPERATURE RANGE	
Ambient	–10° to 40°C
Nitrogen or Vacuum	–20°C to 80°C
Maximum Junction Temperature	70°C
Lead Soldering Temperature[1]	260°C

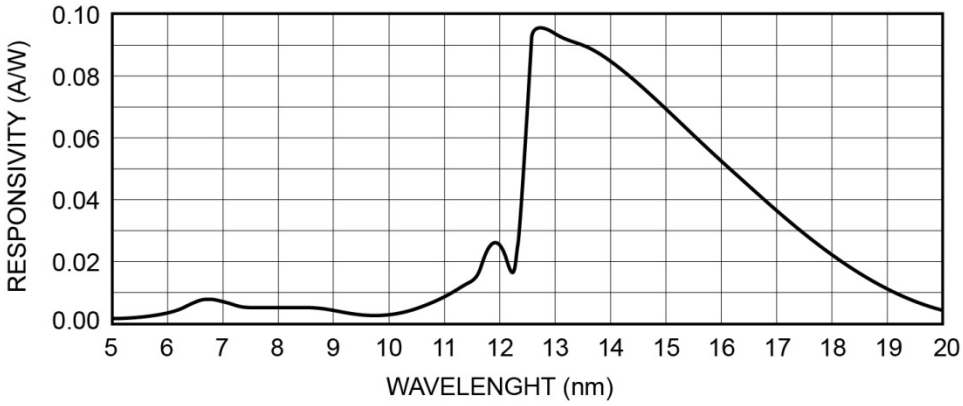
[1]0.08" from case for 10 seconds.

From Deep UV to Mid-IR
OPTO DIODE
An ITW Company

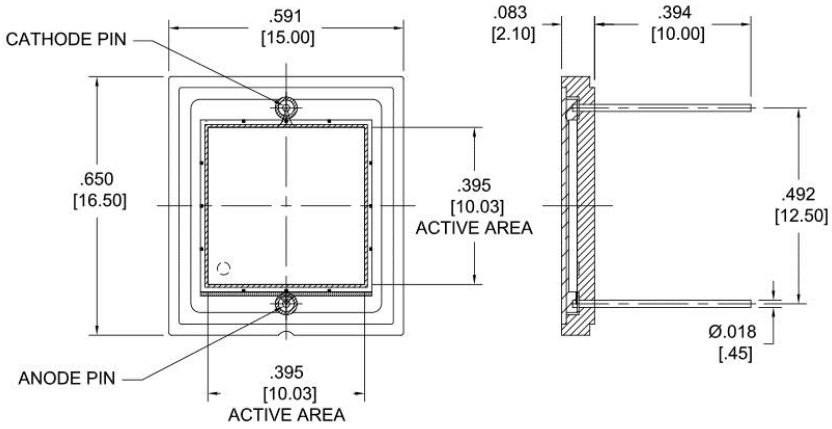
1260 Calle Suerte, Camarillo, California 93012
Phone: (805) 499-0335, Fax: (805) 499-8108
Email: sales@optodiode.com, Website: www.optodiode.com

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TYPICAL RESPONSIVITY at 25° C

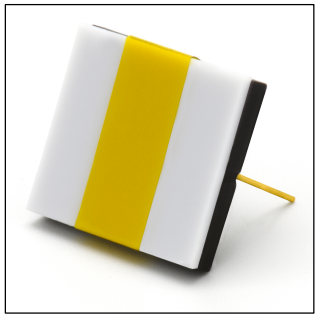


PACKAGE INFORMATION



ORDERING INFORMATION

ODD-SXU-031 Ceramic Carrier with Protective Cover in Black Plastic Container



From Deep UV to Mid-IR
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